

Abstract of the Disclosure

**MANUFACTURING PROCESS FOR A FLASH
MEMORY AND FLASH MEMORY THUS PRODUCED**

The invention relates to a production process for a flash memory from a semiconductor substrate fitted with at least two adjacent rows of precursor stacks of floating gate transistors, the precursor stacks being at least partially covered by a protective resin and being separated by a formation zone for a source line. The process includes forming a trench in the formation zone for the source line by an attack of this zone and of the protective resin. The result of the attack step includes a deposit of residue from the resin below the precursor stacks. The residue deposit is removed. A source line is implanted in the formation zone below the precursor stacks. This process enables the time needed for erasing the memory to be reduced.